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TI Optical recording films
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AB An optical recording film has a composition of $AxBySzTem$ ($0 \leq x \leq 30$, $10 \leq y \leq 70$, $30 \leq z \leq 80$, $0 \leq m < 30$ atomic%, and $B = Sn$ and/or Pb). A may be ≥ 1 of Zn , Cd , Hg , Al , Ga , In , Tl , C , Bi , B , N , P , O , S , F , lanthanide elements, actinide elements, and inert gas elements (e.g., <30 atomic%); Si , Ge , As , and Sb (e.g., <10 atomic%); and Ti , Ni , Co , Sc , Y , Zr , V , Nb , Cr , Mo , Mn , Fe , Ru , Rh , Pd , Ta , and Pt (e.g., <1 atomic%). The composition may have $0.3 < y/(y + z) \leq 0.4$ with $10 \leq m \leq 25$. A $Si3N4$ layer 40-nm thick, a $Sn28Se57Te15$ layer 100-nm thick, and a $Si3N4$ layer 40-nm thick were formed on a glass substrate. A disk was formed by bonding 2 substrates prepared on the sides of $Si3N4$ protective films using a UV-cured resin. A signal output >100 mV was obtained.